

ABSTRACT OF THE DISCLOSURE

In a manufacture of a semiconductor device, spacers are formed on sidewalls of structures including conductive patterns and insulation patterns. The insulation patterns are at least four times thinner than the conductive patterns. After gaps between the structures are filled with a first insulation film, etch stop film patterns having a width which is wider than that of the structures are formed on the structures. A second insulation film is formed to cover the resultant structures without voids between the structures.